

ABSTRACT

A method of making a semiconductor integrated circuit comprises: supplying a semiconductor substrate of a first conductivity type; supplying on top of the substrate a left and a right adjacent semiconductor source and drain pockets of the opposite conductivity type to generate two PN junction regions at where the semiconductor pockets contact the substrate. The two adjacent semiconductor pockets form respectively a source and a drain regions of the semiconductor device. The method additionally include forming a gate layer of a substantially electrically insulating material. The gate layer has such a material in such a structure as to be sufficiently yieldable to minimize effects thereon of thermal mismatch stresses between the different contacting materials thereby improving the performance and reliability of the semiconductor device. A semiconductor integrate circuit made by the method is also disclosed.